

# **30V P-Channel Power MOSFET**

## MOSFET

Metal Oxide Semiconductor Field Effect Transistor

# HRT4407 Data Sheet

Rev. 2020 V3.0



## 南京华瑞微集成电路有限公司 NanJing HRM Semiconductor Co.,Ltd



HRT4407

Pin1

## **30V P-Channel Power MOSFET**

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#### Description

P-Channel Power MOSFET designed by HR-Micro Semiconductor Company, according to the advanced Trench Technology. This devices provide an excellent gate charge and  $R_{DS(on)}$ , which leads to extremely communication and conduction losses. So it is very suitable for AC/DC power conversion, Lighting, and industrial power applications. The package form is SOP-8 which accords with the RoHS standard.

#### Features

- Low FOM R<sub>DS(on)</sub>×Q<sub>gd</sub>
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

#### Applications

- Power Switch Circuit of Adaptor and Charger
- Battery Protection Charge/Discharge
- Notebook AC-in Load Switch



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SOP-8



#### Key Performance Parameters

Key renormance ratameters				
Parameter	Value	Unit		
V <sub>DS@ TA=25°C</sub>	-30	V		
R <sub>DS(on),max@-10V</sub>	12.5	mΩ		
R <sub>DS(on),max@-4.5V</sub>	19.5	mΩ		
Q <sub>g,typ</sub>	62	nC		
I <sub>D@TA=25°C</sub>	-14	А		
$I_{D,pulse}$	-56	А		
E <sub>AS</sub> <sup>1)</sup>	160	mJ		
Device Marking and Package Information				
Device	Package	Marking		

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SOP-8



<b>Absolute Maximum Ratings</b> $T_A = 25^{\circ}C$ , unless otherwise noted						
Parameter Drain-Source Voltage(V <sub>GS</sub> =0V)		Symbol	Values -30	Unit V		
		V <sub>DS</sub>				
Continuous Drain Current <sup>2)</sup>	T <sub>A</sub> = 25°C	- I <sub>D</sub> -	-14	A		
	T <sub>A</sub> = 100°C		-8.8			
Pulsed Drain Current <sup>3)</sup>		I <sub>D,pulse</sub>	-52	А		
Gate-Source Voltage		V <sub>GSS</sub>	±25	V		
Single Pulse Avalanche Energy		E <sub>AS</sub>	160	mJ		
Power Dissipation		P <sub>D</sub>	2.9	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C		

Thermal Resistance					
Parameter	Symbol	Max.	Unit		
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	42	°C/W		

#### Notes

1) L=0.5mH, V<sub>DD</sub>=-15V, Start T<sub>J</sub>=25°C.

2) Limited by maximum junction temperature.

3) Repetitive Rating: Pulse width limited by maximum junction temperature.



#### HRT4407

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_{D} = -250\mu A$	-30			V	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = -30V V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C			-1	- μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> = -30V V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C			-100		
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 25V$			±100	nA	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.2	-1.7	-2.3	V	
		$V_{GS}$ = -20V, $I_{D}$ = -14A		9	11.5	mΩ	
Drain-Source On State Posistance	R	$V_{GS}$ = -10V, $I_{D}$ = -14A		10	12.5	mΩ	
Drain-Source On-State-Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = -6V, $I_{D}$ = -10A		12	15	mΩ	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A		14.5	19.5	mΩ	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -15V f = 1.0MHz		2941		pF	
Output Capacitance	C <sub>oss</sub>			325			
Reverse Transfer Capacitance	C <sub>rss</sub>			297			
Total Gate Charge	Q <sub>g</sub>			62		nC	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> = -15V, I <sub>D</sub> = -14A		10.4			
Gate-Drain Charge	Q <sub>gd</sub>	$V_{GS} = -10V$		11.8			
Gate Plateau Voltage	V <sub>Plateau</sub>			3.2		V	
Turn-on Delay Time	t <sub>d(on)</sub>			12			
Turn-on Rise Time	t <sub>r</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V		7		ns.	
Turn-off Delay Time	$t_{d(off)}$	$R_{G} = 3\Omega$ , $I_{D} = -14A$		53			
Turn-off Fall Time	t <sub>f</sub>			16.5			
Drain-Source Body Diode Character	istics						
Body Diode Forward Voltage	V <sub>SD</sub>	$T_{J} = 25^{\circ}C, I_{SD} = -14A$ $V_{GS} = 0V$		-0.7	-1.2	V	
Continuous Diode Forward Current	I <sub>S</sub>				-13	А	
Reverse Recovery Time	t <sub>rr</sub>			18		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = -14A, di_F/dt = -100A/\mu s$		32		nC	

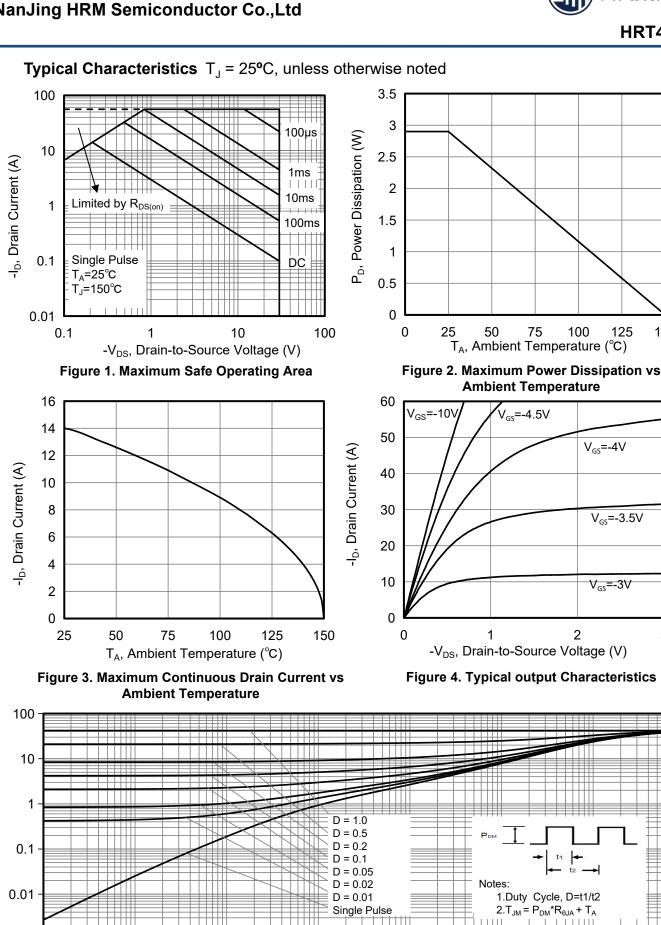


**HRT4407** 

150

3

10



0.1

0.000001

0.00001

0.0001

0.001

Z0JA, Thermal Response (°C/W)

Figure 5. Maximum Effective Thermal Impedance, Junction to Ambient

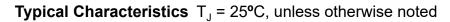
T, Rectangular Pulse Duration (sec)

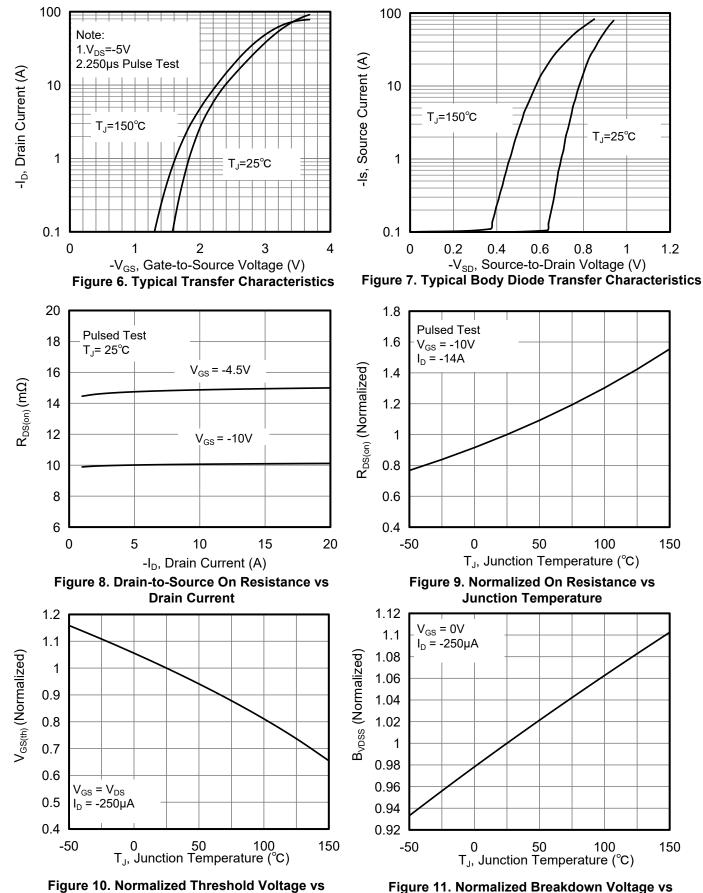
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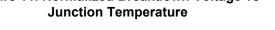
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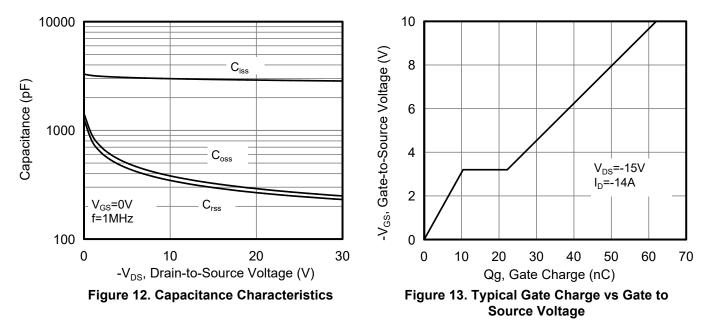


Junction Temperature





#### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted







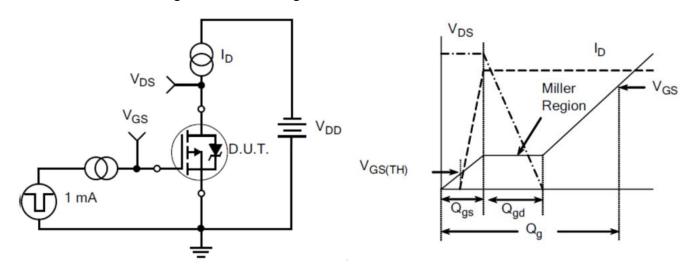
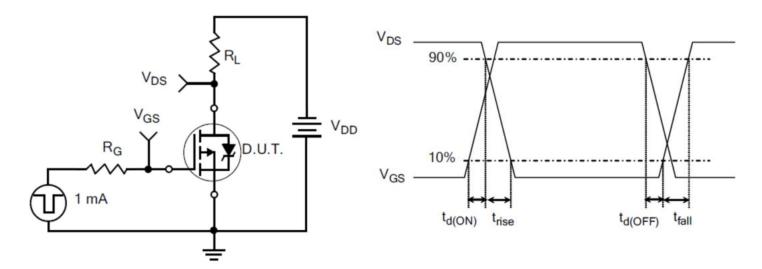
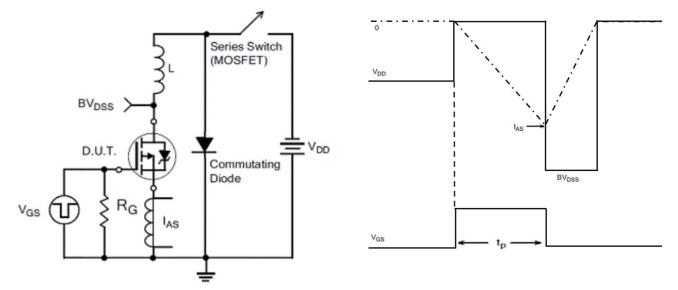


Figure B: Resistive Switching Test Circuit and Waveform



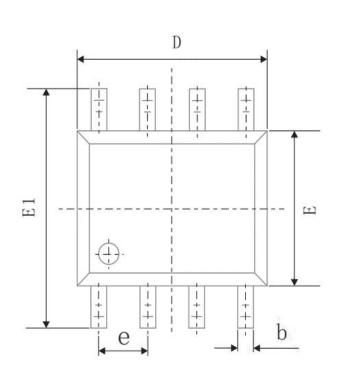


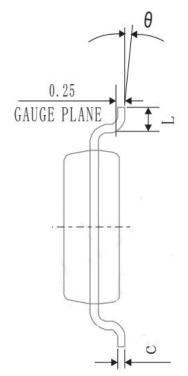


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**Outlines SOP-8 Package** 





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#### COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
А	1.35	1.575	1.8
A1	0.05	0.165	0.25
A2	1.25	1.4125	1.55
b	0.3	0.425	0.51
С	0.153	0.2115	0.253
D	4.8	4.9	5
E	3.8	3.9	4
E1	5.8	6	6.2
L	0.45	0.71	1
θ	0°	4°	8°
е	1.27 BSC		



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